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Record Nr.	UNISA996503464303316
Autore	Chaudhuri Reet
Titolo	Integrated electronics on aluminum nitride : materials and devices / / Reet Chaudhuri
Pubbl/distr/stampa	Cham, Switzerland : , : Springer, , [2022] ©2022
ISBN	9783031171994 9783031171987
Descrizione fisica	1 online resource (266 pages)
Collana	Springer Theses
Disciplina	069
Soggetti	Aluminum nitride
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Nota di bibliografia	Includes bibliographical references.
Nota di contenuto	Intro -- Supervisor's Foreword -- Acknowledgments -- Contents -- Parts of This Thesis Have Been Published in the Following Journal Articles -- 1 Introduction -- 1.1 Brief History of Semiconductors in Communication -- 1.2 Layout of this Dissertation -- References -- 2 Polarization-Induced 2D Hole Gases in Undoped (In)GaN/AlN Heterostructures -- 2.1 Introduction -- 2.2 Polarization Charges in III-Nitride Heterostructures -- 2.3 The Undoped GaN/AlN 2DHG -- 2.4 Impurity Blocking Layers in the AlN Buffer Layer -- 2.5 Very High density InGaN/AlN 2DHGs -- 2.6 Conclusions -- 2.7 Future Directions -- References -- 3 GHz-Speed GaN/AlN p-channel Heterojunction Field Effect Transistors -- 3.1 Introduction -- 3.2 Current Challenges for GaN pFETs -- 3.3 Mg-InGaN Ohmic Contacts to GaN/AlN 2DHG -- 3.4 Scaled RF GaN/AlN p-channel FETs -- 3.5 Benchmark -- 3.6 Future Directions -- References -- 4 Polarization-Induced 2D Electron and Holes in Undoped AlN/GaN/AlN Heterostructures -- 4.1 Introduction -- 4.2 The AlN/GaN/AlN Heterostructure -- 4.3 The Undoped 2D Electron-Hole Bilayer -- 4.4 AlN/GaN/AlN 2DEGs for High-Power RF HEMTs -- 4.4.1 Low-Field Transport -- 4.4.2 High-Field Velocities -- 4.4.3 Shubhnikov-de-Haas Oscillations -- 4.5 Future Directions -- References -- 5 AlN/GaN/AlN High Electron Mobility Transistors -- 5.1 Introduction -- 5.2 Thermal Advantage of AlN Buffer Layer -- 5.3 MBE-Grown AlN Buffer Layers on SiC for RF HEMTs -- 5.4 State-of-Art